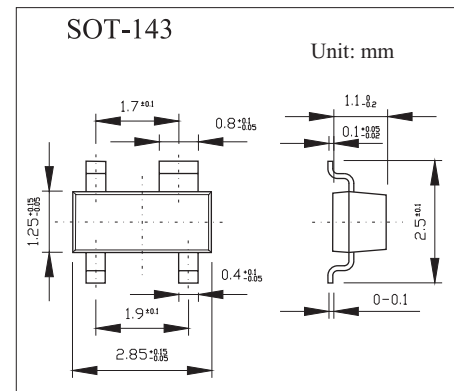


## Silicon RF Switching Diodes

## BAR81



### ■ Features

- Design for use in shunt configuration
- High shunt signal isolation
- Low shunt insertion loss

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	30	V
Forward current	$I_F$	100	mA
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating temperature range	$T_{op}$	-55 to +125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R = 20\text{ V}$			20	nA
Forward voltage	$V_F$	$I_F = 100\text{ mA}$		0.93	1	V
Diode capacitance	$C_T$	$V_R = 1\text{ V}, f = 1\text{ MHz}$		0.6		pF
		$V_R = 3\text{ V}, f = 1\text{ MHz}$		0.57		
Forward resistance	$r_f$	$I_F = 5\text{ mA}, f = 100\text{ MHz}$		0.7		$\Omega$
Series inductance chip to ground	$L_s$			1.5		nH

### ■ Marking

Type	BAR81
Marking	BBs